Silicon Bridge Rectifier CBR1-D080S

800V / 1A

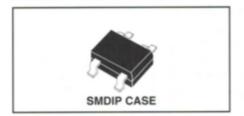
DATASHEET

OEM - Central Semiconductor Corp.

Source: Central Databook 2004

CBR1-D020S SERIES

SURFACE MOUNT
1 AMP DUAL IN LINE
SILICON BRIDGE RECTIFIER



Central™ Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1-D020S series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

NOTE: Also available in Fast Recovery, please contact factory for details.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS (T _A =25°	(C)						
MAXIMUM HATINGS (1 _A =25	SYMBOL	CBR1- D020S	CBR1- D040S	CBR1- D060S	CBR1- D080S	CBR1- D100S	UNITS
Peak Repetitive Reverse Voltage	ge V _{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	VR	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	560	700	V
Average Forward Current (TA=	50°C) I _O			1.0			Α
Peak Forward Surge Current	^I FSM			50			Α
Rating for Fusing (t<8.35ms)	12			10			A ² s
Operating and Storage							
Junction Temperature	T_J , T_{sta}			-65 to +150	0		°C

ELECTRICAL	CHARACTERISTICS	(T _A =25°C unless otherw	vise noted)			
SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
IR	V _R =Rated V _{RRM}				10	μΑ
IR	V _R =Rated V _{RRM} , T _A =125°C			0.5	mA	
VF	I _F =1.0A				1.1	V
CJ	V _R =4.0V, f=1.0MHz			25		pF

For Typical Electrical Characteristic Data for this device, please see Process CPD05 on page 875.

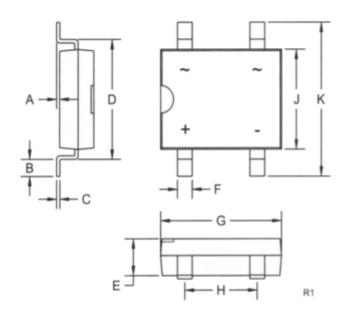
R2 (13-November 2002)



CBR1-D020S SERIES

SURFACE MOUNT 1 AMP DUAL IN LINE SILICON BRIDGE RECTIFIER

SMDIP CASE - MECHANICAL OUTLINE



MARKING CODE: FULL PART NUMBER

DIMENSIONS					
	INCHES		MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	
Α	0.004	0.008	0.10	0.20	
В	0.040	0.060	1.02	1.52	
С	0.009		0.23		
D	0.290	0.310	7.37	7.87	
E	0.086	0.098	2.18	2.49	
F	0.038	0.042	0.97	1.07	
G	0.316	0.335	8.03	8.51	
Н	0.195	0.205	4.95	5.21	
J	0.245	0.255	6.22	6.48	
K	0.360	0.410	9.14	10.41	
SMDIP (REV: R1)					

SHEETS

R2 (13-November 2002)